安徽富信半导体科技有限公司

ANHUI FOSAN SEMICONDUCTOR TECHNOLOGY CO. , LTD.

FS4832

SOP-8 30V Dual N Channel Enhancement 双 N 沟道增强型
MOS Field Effect Transistor 场效应管

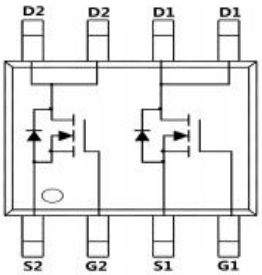
■Features 特点

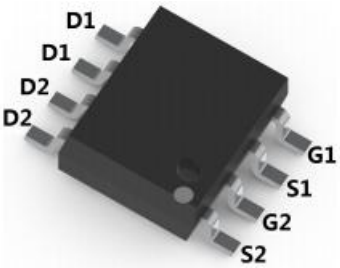
Low on-resistance 低导通电阻
$R_{DS(ON)}$=12mΩ(Type)@V_{GS}=10V
$R_{DS(ON)}$=15mΩ(Type)@V_{GS}=4.5V

■Applications 应用

Load Switch 负载开关
PWM Application 脉宽调制应用
Power Management in Note Book 笔记本电源管理

■Internal Schematic Diagram 内部结构





■Absolute Maximum Ratings 最大额定值

Characteristic 特性参数	Symbol 符号	Rat 额定值	Unit 单位
Drain-Source Voltage 漏极-源极电压	BV_{DSS}	30	V
Gate- Source Voltage 栅极-源极电压	V_{GS}	±20	V
Drain Current (continuous)漏极电流-连续	I_D（at T_A = 25°C） （at T_A = 75°C）	8.3 6.4	A
Drain Current (pulsed)漏极电流-脉冲	I_{DM}	32	A
Total Device Dissipation 总耗散功率	P_D(at T_A = 25°C) （at T_A = 75°C）	2000 1200	mW
Thermal Resistance Junction-Ambient 热阻	$R_{\Theta JA}$	62.5	℃/W
Junction/Storage Temperature 结温/储存温度	T_J,T_{stg}	-55~150	℃

■Electrical Characteristics 电特性

(T_A=25℃ unless otherwise noted 如无特殊说明，温度为 25℃)

Characteristic 特性参数	Symbol 符号	Min 最小值	Typ 典型值	Max 最大值	Unit 单位
Drain-Source Breakdown Voltage 漏极-源极击穿电压(I_D =250uA,V_{GS}=0V)	BV_{DSS}	30	—	—	V
Gate Threshold Voltage 栅极开启电压(I_D =250uA,V_{GS}= V_{DS})	$V_{GS(th)}$	1	1.5	2.4	V
Zero Gate Voltage Drain Current 零栅压漏极电流(V_{GS}=0V, V_{DS}= 30V)	I_{DSS}	—	—	1	uA
Gate Body Leakage 栅极漏电流(V_{GS}=±20V, V_{DS}=0V)	I_{GSS}	—	—	±100	nA
Static Drain-Source On-State Resistance 静态漏源导通电阻(I_D=8A,V_{GS}=10V) (I_D=6A,V_{GS}=4.5V)	$R_{DS(ON)}$	—	12 15	19 26	mΩ
Diode Forward Voltage Drop 内附二极管正向压降(I_{SD}=1A,V_{GS}=0V)	V_{SD}	—	—	1.2	V
Input Capacitance 输入电容 (V_{GS}=0V, V_{DS}=15V,f=1MHz)	C_{ISS}	—	750	—	pF
Common Source Output Capacitance 共源输出电容(V_{GS}=0V, V_{DS}=15V,f=1MHz)	C_{OSS}	—	125	—	pF
Reverse Transfer Capacitance 反馈电容 (V_{GS}=0V, V_{DS}=15V,f=1MHz)	C_{RSS}	—	70	—	pF
Total Gate Charge 栅极电荷密度 (V_{DS}=15V, I_D=8A, V_{GS}=4.5V)	Q_g	—	15	—	nC
Gate Source Charge 栅源电荷密度 (V_{DS}=15V, I_D=8A, V_{GS}=4.5V)	Q_{gs}	—	2.5	—	nC
Gate Drain Charge 栅漏电荷密度 (V_{DS}=15V, I_D=8A, V_{GS}=4.5V)	Q_{gd}	—	3	—	nC
Turn-ON Delay Time 开启延迟时间 (V_{DS}=15V I_D=1A, R_{GEN}=3Ω,V_{GS}=10V)	$t_{d(on)}$	—	4.5	—	ns
Turn-ON Rise Time 开启上升时间 (V_{DS}=15V I_D=1A, R_{GEN}=3Ω,V_{GS}=10V)	t_r	—	10	—	ns
Turn-OFF Delay Time 关断延迟时间 (V_{DS}=15V I_D=1A, R_{GEN}=3Ω,V_{GS}=10V)	$t_{d(off)}$	—	18	—	ns
Turn-OFF Fall Time 关断下降时间 (V_{DS}=15V I_D=1A, R_{GEN}=3Ω,V_{GS}=10V)	t_f	—	6	—	ns

■Typical Characteristic Curve 典型特性曲线

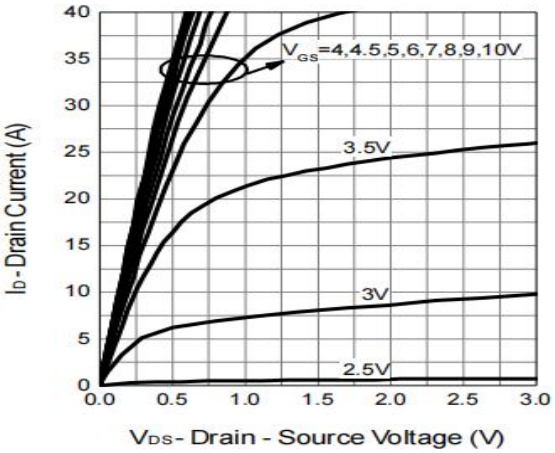


Figure 1: Output Characteristics

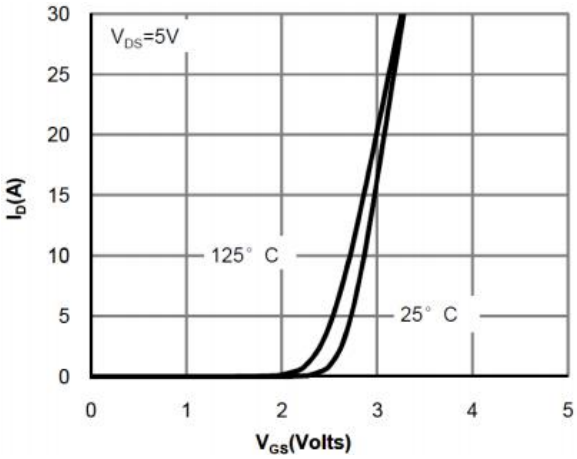


Figure 2: Transfer Characteristics

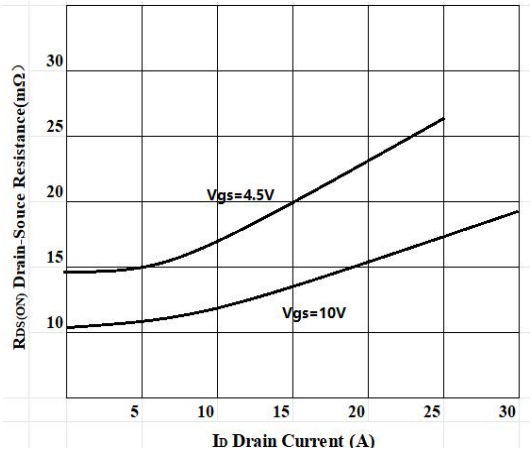


Figure 3: On-Resistance vs. Drain Current

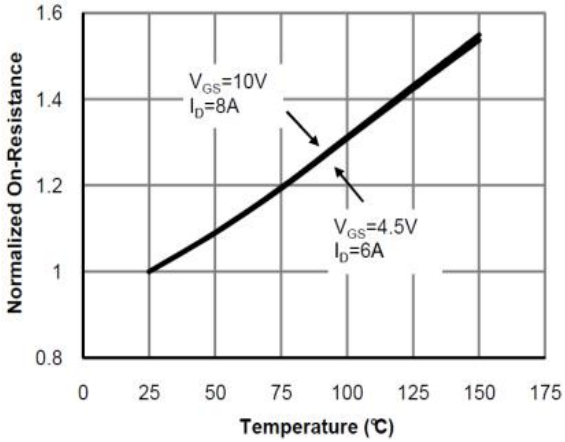


Figure 4: On-Resistance vs. Temperature

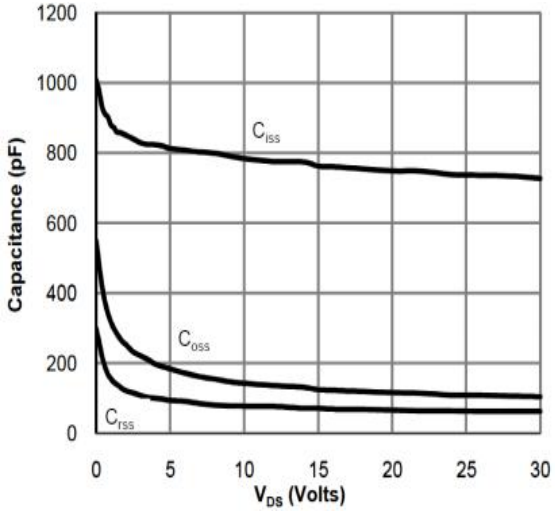


Figure 5: Capacitance Characteristics

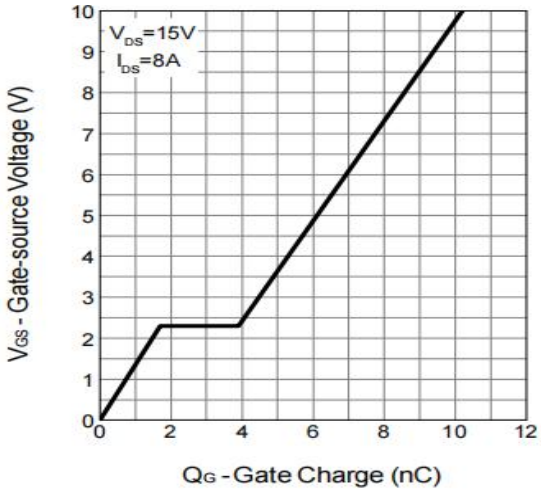


Figure 6: Gate-Charge Characteristics

■Typical Characteristic Curve 典型特性曲线

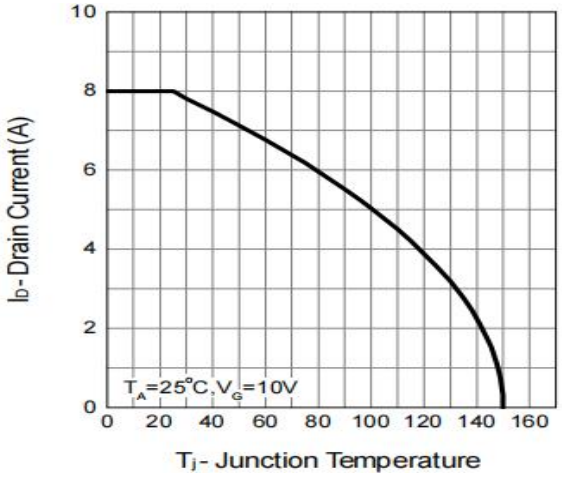


Figure 7: Drain Current vs. Temperature

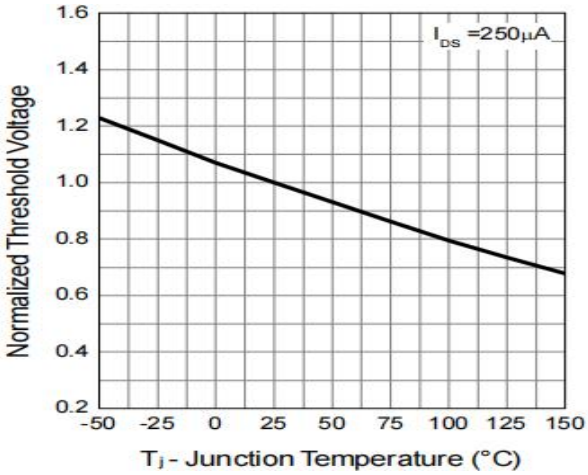


Figure 8: Threshold Voltage vs. Temperature

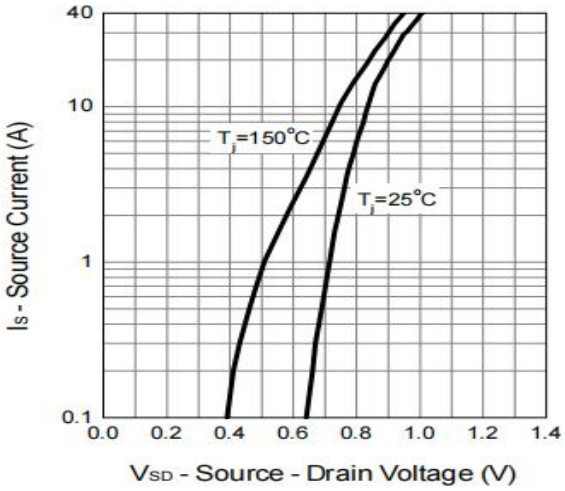


Figure 9: Diode Characteristics

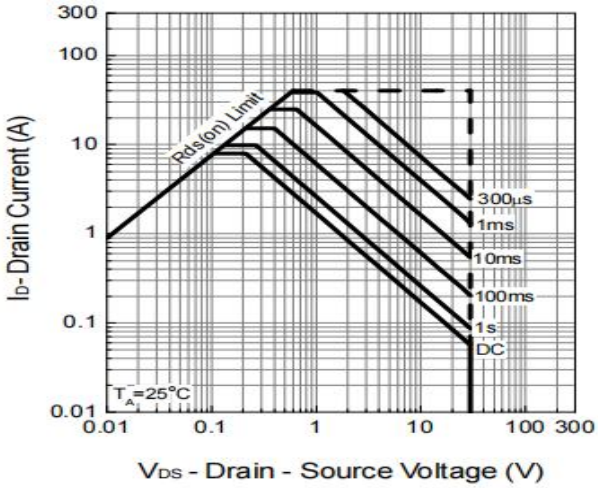


Figure 10: Safe Operating Area

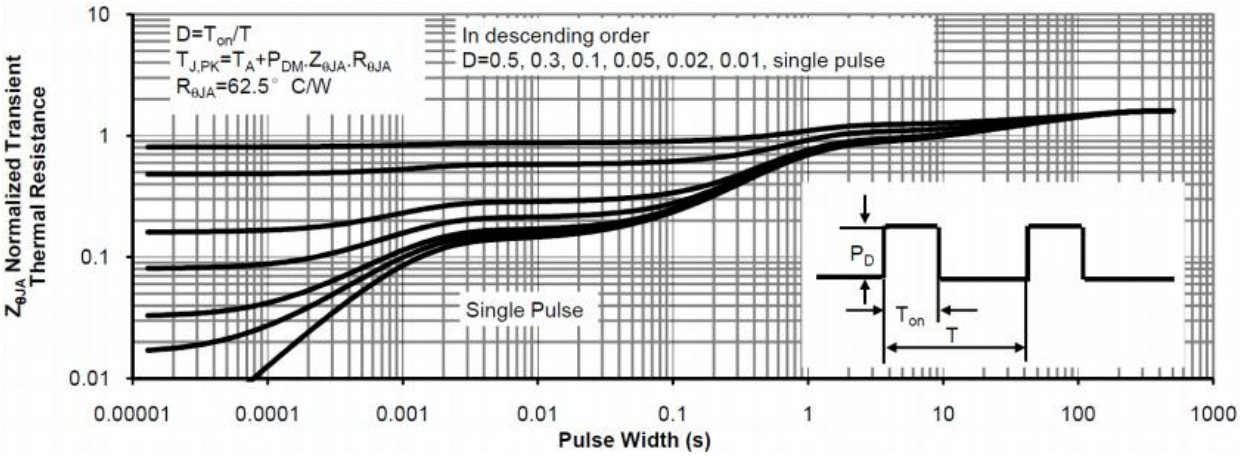
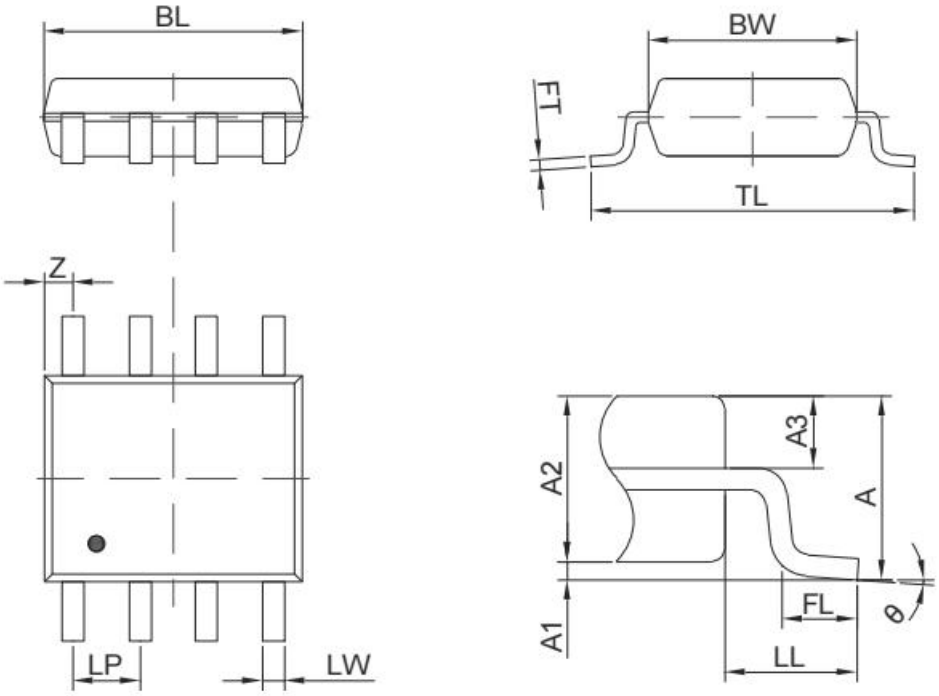


Figure 11: Transient Thermal Response Curve

■Dimension 外形封装尺寸



COMMON DIMENSIONS: UNITS OF MEASURE=MILLIMETER

Symbol	Dimensions		Symbol	Dimensions	
	Min.	Max.		Min.	Max.
A	1.75		FL	0.50	0.80
A1	0.05	0.15	LP	1.25	1.30
A2	1.40	1.50	LL	1.1 BSC	
A3	0.623 BSC		LW	0.38	0.43
BL	4.92	5.80	TL	5.90	6.10
BW	3.70	4.10	Z	0.54	
FT	0.20	0.21	θ	0°	8°